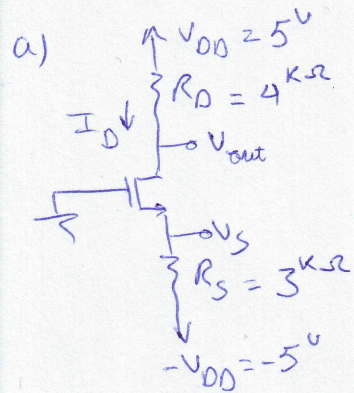


Question 1)



$$V_G = 0$$

$$V_S = -V_{DD} + R_S I_D = -5 + 3I_D$$

$$V_D = V_{DD} - R_D I_D = 5 - 4I_D$$

$$I_D = \frac{1}{2} k'_n \frac{W}{L} (V_{GS} - V_t)^2$$

$$= \frac{1}{2} \times 0.1^m \times 20 \times (0 - (-5 + 3I_D) - 1)^2$$

$$\Rightarrow I_D = (4 - 3I_D)^2$$

$$\Rightarrow 9I_D^2 - 25I_D + 16 = 0$$

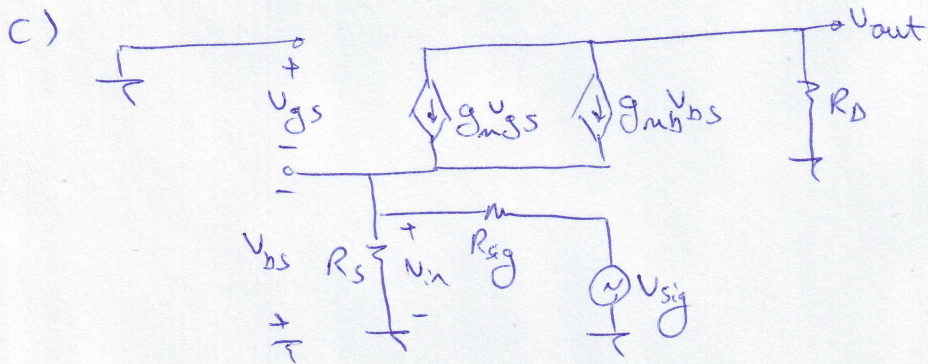
$$\Rightarrow I_D = \begin{cases} 1 \text{ mA} \checkmark \\ 1.8 \text{ mA} \end{cases}$$

$$V_S = -2 \text{ V}, V_D = 1 \text{ V}$$

$$V_S = 0.4 \text{ V} \Rightarrow V_{GS} = -0.4 < V_t$$

not acceptable

b) input is at Source }
output is at Drain } \Rightarrow CG amplifier



$$d) g_m = \frac{2I_D}{V_{GS} - V_t} = \frac{2 \times 1 \text{ mA}}{0 - (-2) - 1} = 2 \text{ mA/V}$$

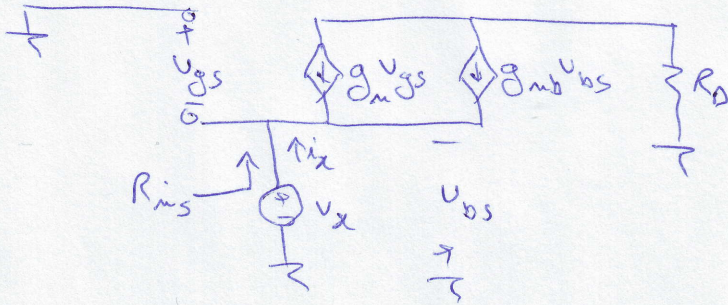
$$g_{mb} = \chi g_m = 0.2 \times 2 = 0.4 \text{ mA/V}$$

$$e) V_{in} = -V_{GS} = -V_{BS}$$

$$V_{out} = -(g_m V_{GS} + g_{mb} V_{BS}) R_D = (g_m + g_{mb}) R_D V_{in}$$

$$\Rightarrow \frac{V_{out}}{V_{in}} = (g_m + g_{mb}) R_D = (2 + 0.4) \times 4^k = 9.6 \text{ V/V}$$

f)



$$V_{gs} = V_{bs} = -V_x$$

$$i_x = -g_m V_{gs} - g_{mb} V_{bs} = (g_m + g_{mb}) V_x \Rightarrow R_{in} = \frac{1}{g_m + g_{mb}}$$

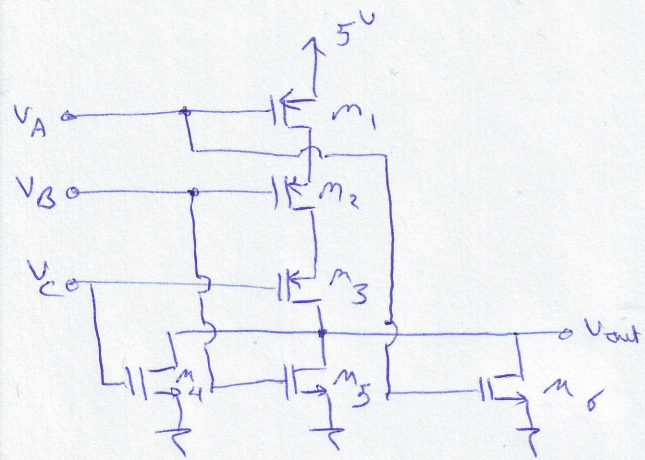
$$R_i = R_s \parallel R_{in} = R_s \parallel \frac{1}{g_m + g_{mb}} = 3^k \parallel \frac{1}{24^m} = 366^{\Omega}$$

$$g) \quad V_{in} = \frac{R_i}{R_i + R_{sig}} V_{sig} = \frac{366}{366 + 50} V_{sig}$$

$$\frac{V_{in}}{V_{sig}} = 0.88 \text{ V/V}$$

$$\Rightarrow \frac{V_{out}}{V_{sig}} = \frac{V_{out}}{V_{in}} \times \frac{V_{in}}{V_{sig}} = 9.6 \times 0.88 = 8.45 \text{ V/V}$$

Question 2)

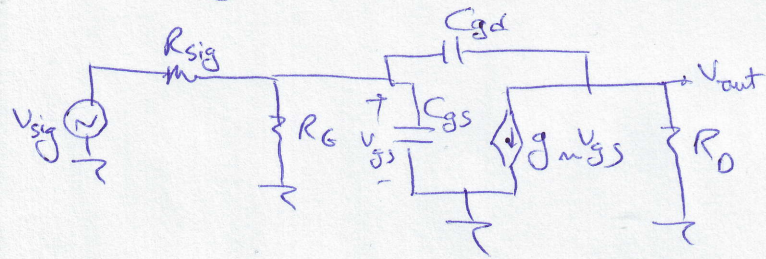


a) $V_A = 0$
 $V_B = 0$
 $V_C = 0$ } \Rightarrow m_1, m_2, m_3 are "on"
 m_4, m_5, m_6 are "off" $\Rightarrow V_{out} = 5V$

b) $V_A = 0$
 $V_B = 5V$
 $V_C = 0$ } \Rightarrow m_2 is "off"
 m_5 is "on" $\Rightarrow V_{out} = 0V$

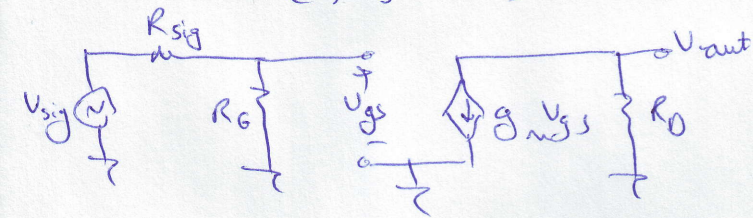
Question 3)

a) at high frequencies C_c and C_s are short circuits.



b) A_m & $C_{gs}, C_{gd} \rightarrow$ o.c.

$C_c, C_s \rightarrow$ s.c.



$$\left. \begin{aligned} V_{gs} &= \frac{R_G}{R_G + R_{sig}} V_{sig} \\ V_{out} &= -g_m V_{gs} R_D \end{aligned} \right\} \Rightarrow \frac{V_{out}}{V_{sig}} = - \frac{R_G}{R_G + R_{sig}} g_m R_D$$

$$\left. \begin{aligned} f_{C_s} &= \frac{1}{2\pi C_s R_{Cs}} \\ R_{Cs} &= \frac{1}{g_m} \end{aligned} \right\} \Rightarrow f_{C_s} = \frac{1}{2\pi C_s \frac{1}{g_m}}$$

$$\left. \begin{aligned} f_{C_c} &= \frac{1}{2\pi C_c R_{Cc}} \\ R_{Cc} &= R_{sig} + R_G \end{aligned} \right\} \Rightarrow f_{C_c} = \frac{1}{2\pi C_c (R_{sig} + R_G)}$$

$$e) f_H \approx \frac{1}{2\pi C_{in} R_{in}}$$

$$C_{in} = C_{gs} \parallel [C_{gd}(1 + g_m R_D)] = C_{gs} + C_{gd}(1 + g_m R_D)$$

$$R_{in} = R_{sig} \parallel R_G$$

Question 4)

For an npn BJT in active mode BE junction is in forward bias and BC junction is in reverse bias. Since BE junction is in forward bias, a large number of electrons (majority carriers) from the Emitter region enter the Base region. Since the BC junction is reverse-biased most of these electrons (minority carriers in the P-type Base) are swept into the Collector region. Considering that the Base region is very thin. Therefore, a large current flows between the Collector and Emitter region. This current is controlled by a small voltage V_{BE} .